



SEMITRANS® 2

Trench IGBT Modules

SKM195GB07E3

Target Data

Features

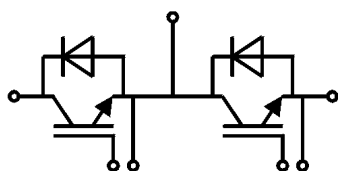
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability, self limiting to $6 \times I_{Cnom}$
- Fast & soft inverse CAL diodes
- Insulated copper baseplate using DBC Technology (Direct Copper Bonding)
- With integrated gate resistor

Typical Applications*

- AC inverter drives
- UPS
- Electronic welders

Remarks

- Case temperature limited to $T_c = 125^\circ\text{C}$ max.
- Recommended $T_{op} = -40 \dots +150^\circ\text{C}$
- Product reliability results valid for $T_j = 150^\circ\text{C}$
- Use of soft R_G necessary



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Absolute Maximum Ratings

Symbol	Conditions	Values	Unit	
IGBT				
V_{CES}	$T_j = 25^\circ\text{C}$	650	V	
I_C	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	259	A
		$T_c = 80^\circ\text{C}$	196	A
I_{Cnom}		200	A	
I_{CRM}	$I_{CRM} = 3 \times I_{Cnom}$	600	A	
V_{GES}		-20 ... 20	V	
t_{psc}	$V_{CC} = 360\text{ V}$ $V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 650\text{ V}$	$T_j = 150^\circ\text{C}$	6	μs
T_j		-40 ... 175	$^\circ\text{C}$	
Inverse diode				
I_F	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	217	A
		$T_c = 80^\circ\text{C}$	157	A
I_{Fnom}		200	A	
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	400	A	
I_{FSM}	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 25^\circ\text{C}$	1470	A	
T_j		-40 ... 175	$^\circ\text{C}$	
Module				
$I_{t(RMS)}$		200	A	
T_{stg}		-40 ... 125	$^\circ\text{C}$	
V_{isol}	AC sinus 50 Hz, $t = 1\text{ min}$	4000	V	

Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
IGBT					
$V_{CE(sat)}$	$I_C = 200\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	1.46	1.90	V
		$T_j = 150^\circ\text{C}$	1.70	2.10	V
V_{CE0}	chipelevel	$T_j = 25^\circ\text{C}$	0.90	1.00	V
		$T_j = 150^\circ\text{C}$	0.82	0.90	V
r_{CE}	$V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	2.8	4.5	$\text{m}\Omega$
		$T_j = 150^\circ\text{C}$	4.4	6.0	$\text{m}\Omega$
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 3.2\text{ mA}$	5.1	5.8	6.4	V
I_{CES}	$V_{GE} = 0\text{ V}$ $V_{CE} = 650\text{ V}$	$T_j = 25^\circ\text{C}$		0.3	mA
		$T_j = 150^\circ\text{C}$		-	mA
C_{ies}	$V_{CE} = 25\text{ V}$		12.3		nF
C_{oes}	$V_{GE} = 0\text{ V}$		0.77		nF
C_{res}			0.37		nF
Q_G	$V_{GE} = -8\text{ V} \dots +15\text{ V}$		1600		nC
R_{Gint}	$T_j = 25^\circ\text{C}$		2.0		Ω
$t_{d(on)}$	$V_{CC} = 300\text{ V}$ $I_C = 200\text{ A}$	$T_j = 150^\circ\text{C}$	124		ns
t_r	$V_{GE} = +15/-15\text{ V}$	$T_j = 150^\circ\text{C}$	52		ns
E_{on}	$R_{Gon} = 2\ \Omega$	$T_j = 150^\circ\text{C}$	8		mJ
$t_{d(off)}$	$R_{Goff} = 2\ \Omega$	$T_j = 150^\circ\text{C}$	335		ns
t_f		$T_j = 150^\circ\text{C}$	85		ns
E_{off}		$T_j = 150^\circ\text{C}$	11		mJ
$R_{th(j-c)}$	per IGBT			0.23	K/W



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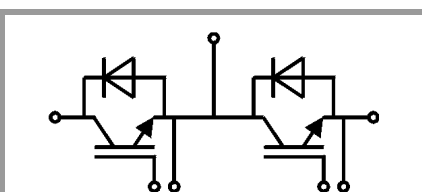
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Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
$V_F = V_{EC}$	$I_F = 200 \text{ A}$ $V_{GE} = 0 \text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$		1.39	1.75	V
		$T_j = 150^\circ\text{C}$		1.38	1.76	V
V_{F0}	chipelevel	$T_j = 25^\circ\text{C}$		1.04	1.24	V
		$T_j = 150^\circ\text{C}$		0.85	0.99	V
r_F	chipelevel	$T_j = 25^\circ\text{C}$		1.76	2.6	m Ω
		$T_j = 150^\circ\text{C}$		2.6	3.9	m Ω
I_{RRM}	$I_F = 200 \text{ A}$	$T_j = 150^\circ\text{C}$		150		A
Q_{rr}	$V_{GE} = \pm 15 \text{ V}$ $V_{CC} = 300 \text{ V}$	$T_j = 150^\circ\text{C}$		20		μC
E_{rr}		$T_j = 150^\circ\text{C}$		6		mJ
$R_{th(j-c)}$	per diode				0.4	K/W
Module						
L_{CE}				30		nH
$R_{CC'+EE'}$	measured per switch	$T_c = 25^\circ\text{C}$		0.65		m Ω
		$T_c = 125^\circ\text{C}$		1.09		m Ω
$R_{th(c-s)}$	calculated without thermal coupling ($\lambda_{grease} = 0.81 \text{ W}/(\text{m}^2\text{K})$)			0.04		K/W
M_s	to heat sink M6		3		5	Nm
M_t	to terminals M5			2.5	5	Nm
						Nm
w					160	g



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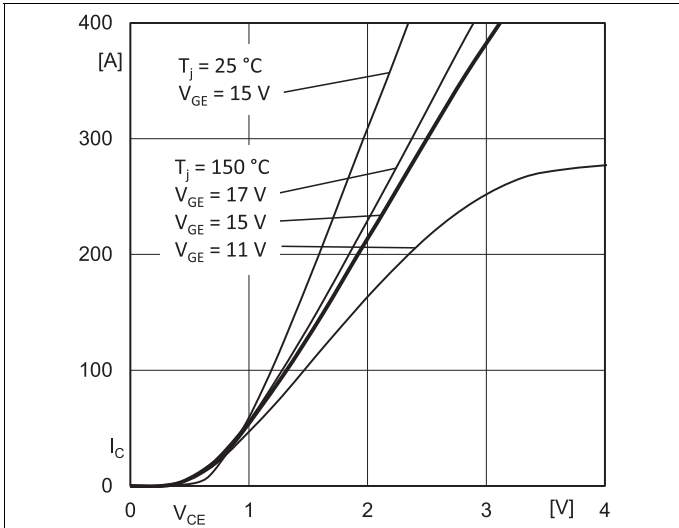


Fig. 1: Typ. output characteristic, inclusive $R_{CC'+EE}$

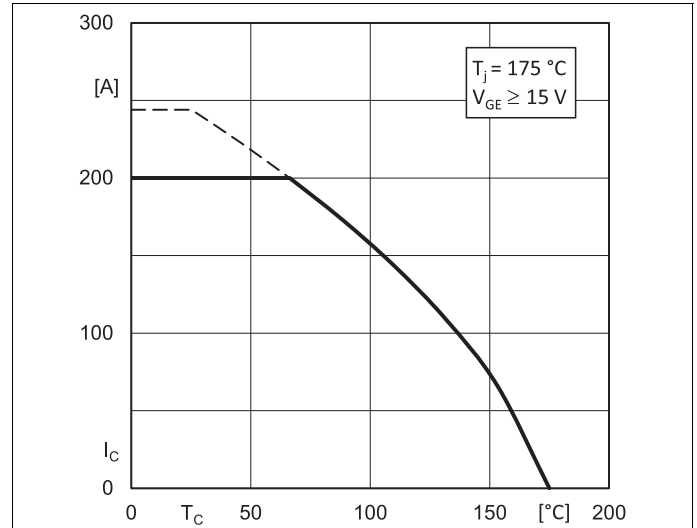


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

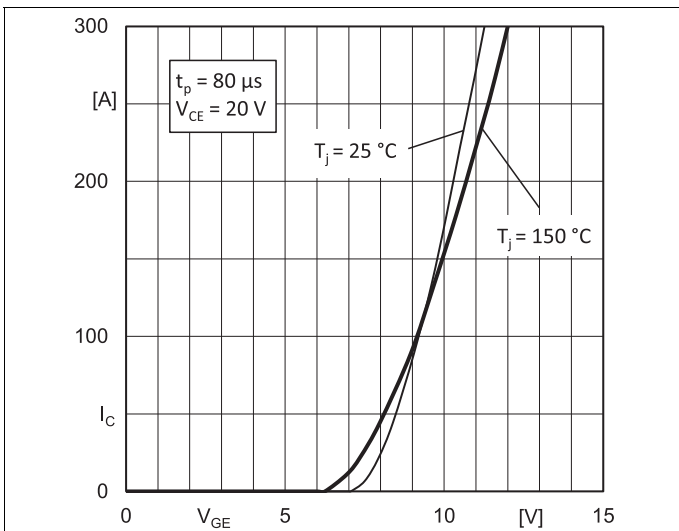


Fig. 5: Typ. transfer characteristic

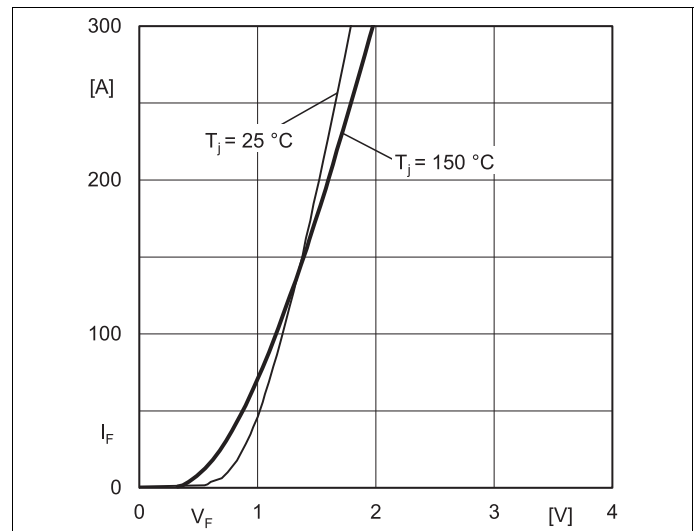
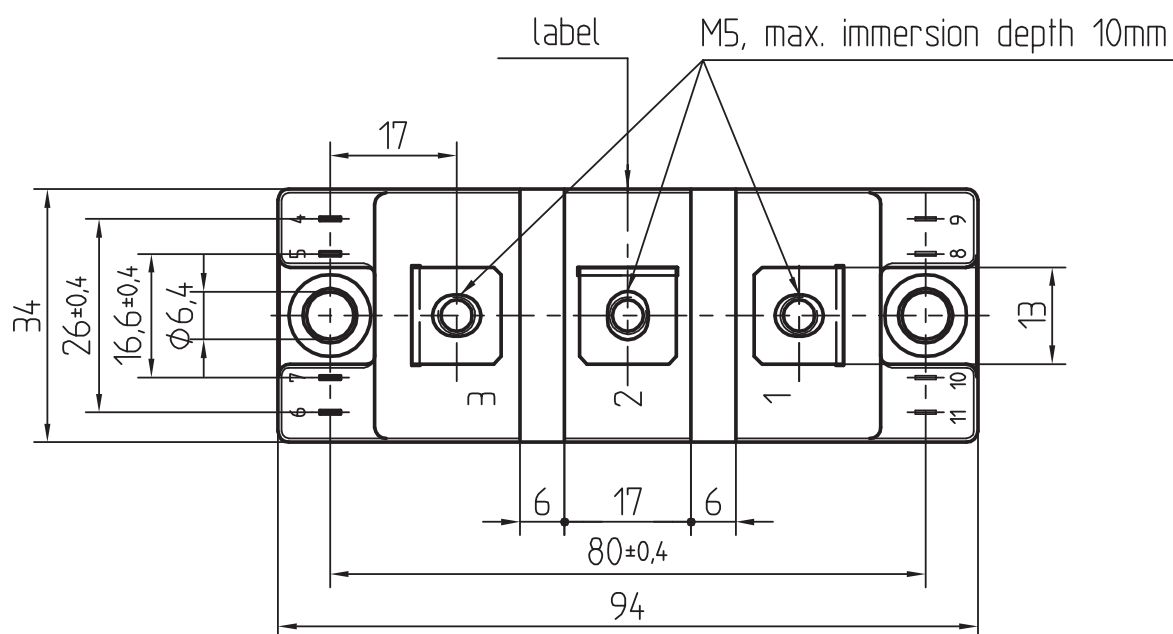
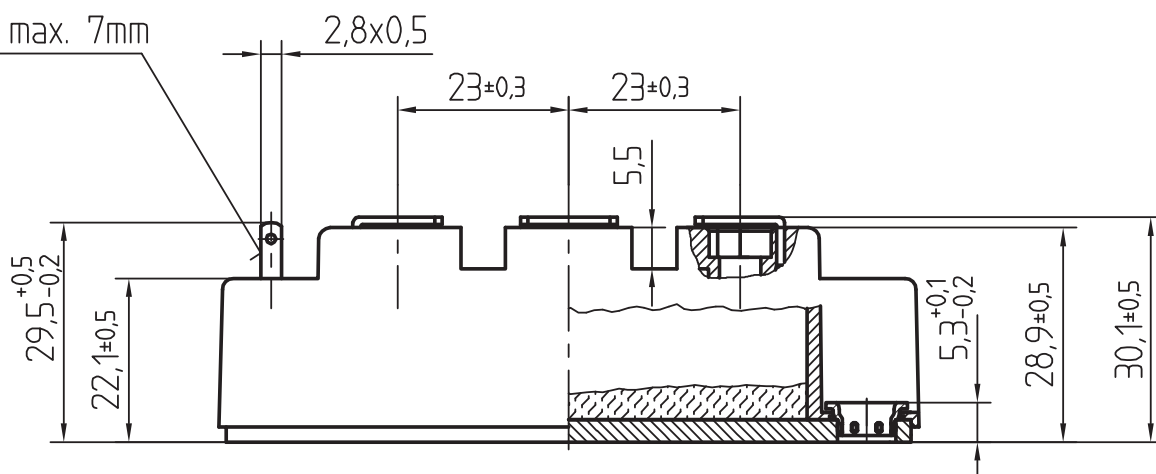


Fig. 10: Typ. CAL diode forward charact., incl. $R_{CC'+EE}$

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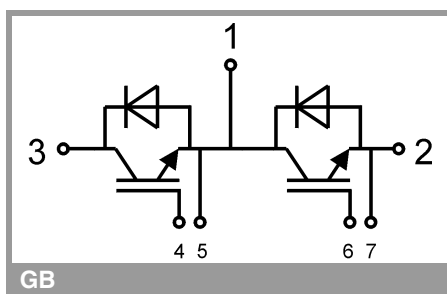
Dimensions in mm

Plug in depth max. 7mm



General tolerance +/- 0,5 mm

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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

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